



# STPR120A

## HIGH EFFICIENCY FAST RECOVERY DIODE

### MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	1 A
$V_{RRM}$	200 V
$t_{rr} (max)$	35 ns

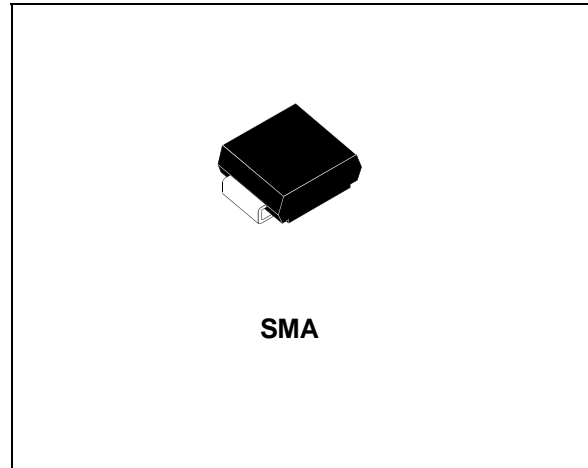
### FEATURES AND BENEFITS

- VERY LOW SWITCHING LOSSES
- LOW FORWARD VOLTAGE DROP
- SURFACE MOUNT DEVICE
- FAST RECTIFIER EPITAXIAL DIODE

### DESCRIPTION

Single chip rectifier suited to Switched Mode Power Supplies and high frequency DC/DC converters.

Packaged in SMA, this surface mount device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



### ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage	200	V
$I_{F(RMS)}$	RMS forward current	8	A
$I_{F(AV)}$	Average forward current	1	A
$I_{FSM}$	Surge non repetitive forward current	$T_{Lead} = 125^{\circ}C$ $\delta = 0.5$	A
$T_{stg}$	Storage temperature range	- 65 to + 150	$^{\circ}C$
$T_j$	Maximum junction temperature	150	$^{\circ}C$

### THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-l)}$	Junction to lead	30	$^{\circ}C/W$

## STPR120A

### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Tests Conditions	Tests Conditions		Min.	Typ.	Max.	Unit
$I_R^*$	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			3	$\mu\text{A}$
		$T_j = 125^\circ\text{C}$			180	400	
$V_F^{**}$	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 1\text{ A}$			0.9	V
		$T_j = 150^\circ\text{C}$	$I_F = 1\text{ A}$		0.65	0.71	

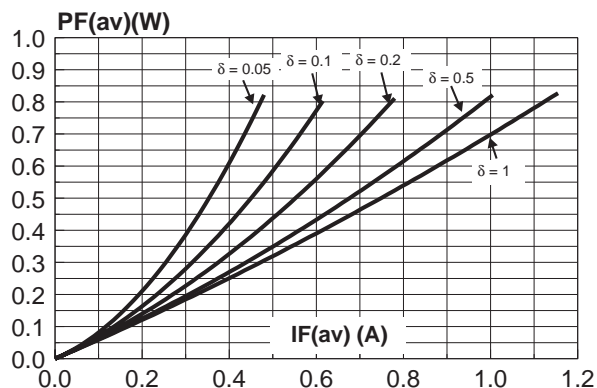
Pulse test : \*  $t_p = 5\text{ms}$ ,  $\delta < 2\%$   
\*\*  $t_p = 380\ \mu\text{s}$ ,  $\delta < 2\%$

### RECOVERY CHARACTERISTICS

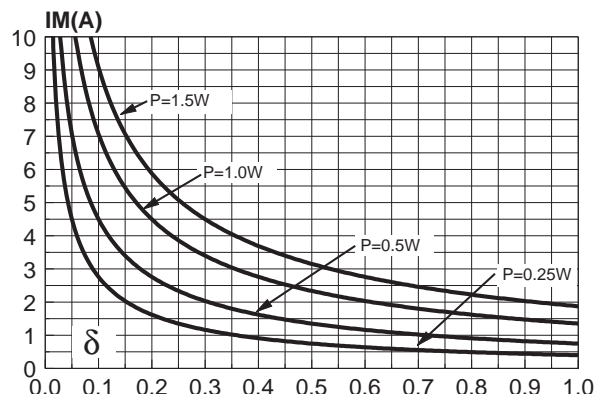
Symbol	Tests Conditions		Min.	Typ.	Max.	Unit
trr	$T_j = 25^\circ\text{C}$	$I_F = 0.50\text{ A}$ $I_R = 1\text{ A}$			25	ns
		$I_F = 1\text{ A}$ $V_R = V_{RRM}$				
tFR	$T_j = 25^\circ\text{C}$	$I_F = 1\text{ A}$ Measured at 1 V			25	
VFP	$T_j = 25^\circ\text{C}$	$I_F = 1\text{ A}$ $dl_F/dt = 100\text{ A}/\mu\text{s}$			5	V

To evaluate the maximum conduction losses use the following equation :  
 $P = 0.58 \times I_{F(AV)} + 0.118 \times I_{F(RMS)}^2$

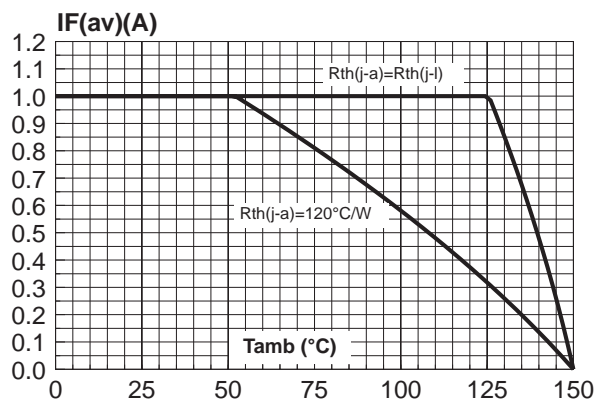
**Fig. 1:** Average forward power dissipation versus average forward current.



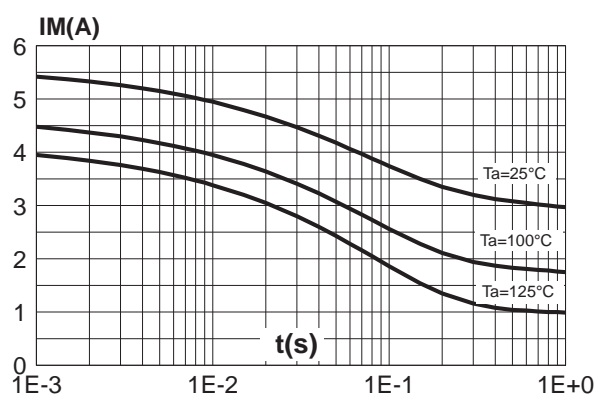
**Fig. 2:** Peak current versus form factor.



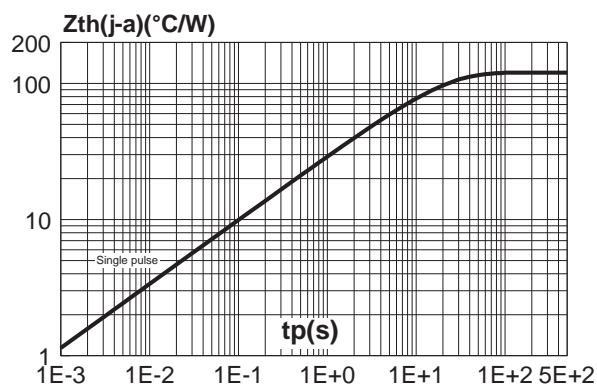
**Fig. 3:** Average forward current versus ambient temperature ( $\delta=0.5$ ).



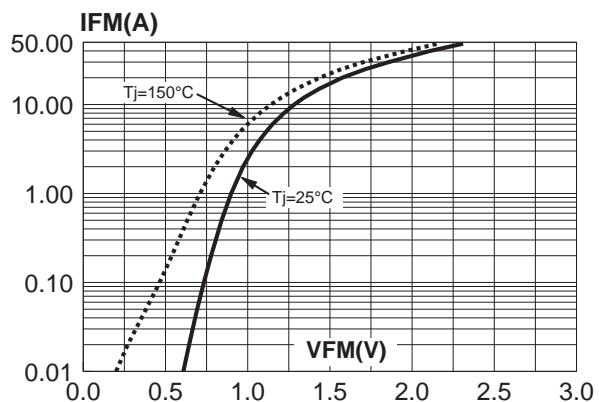
**Fig. 4:** Non repetitive surge peak forward current versus overload duration.



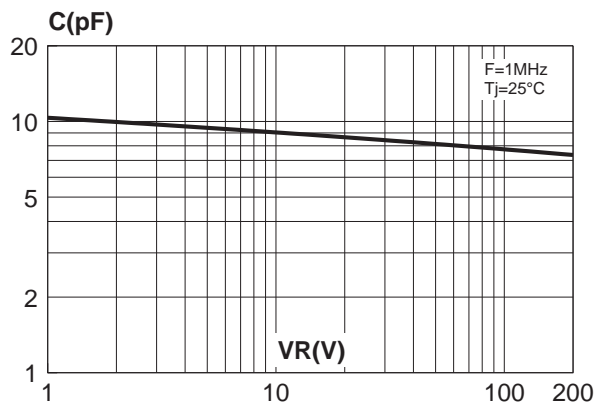
**Fig. 5:** Variation of thermal impedance junction to ambient versus pulse duration (Recommended pad layout, epoxy FR4,  $e(Cu)=35\mu m$ ).



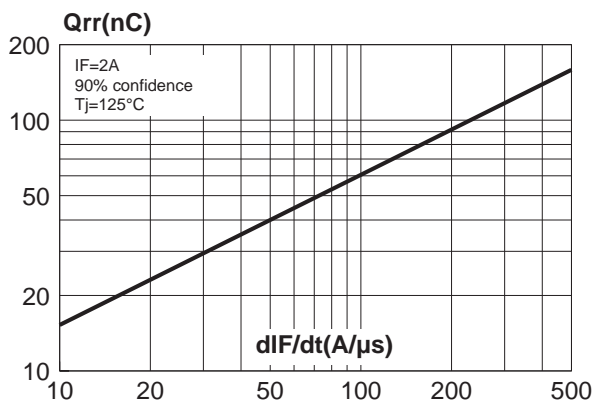
**Fig. 6:** Forward voltage drop versus forward current (maximum values).



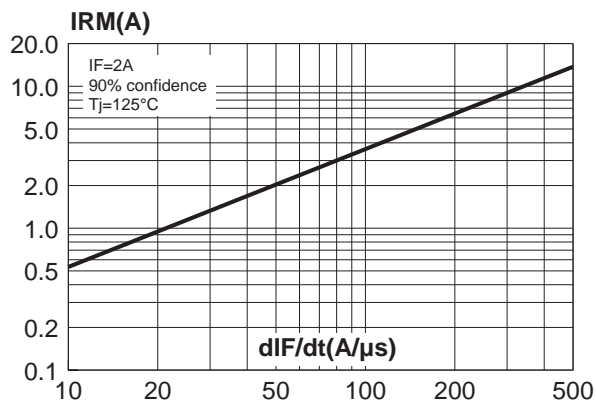
**Fig. 7:** Junction capacitance versus reverse voltage applied (typical values).



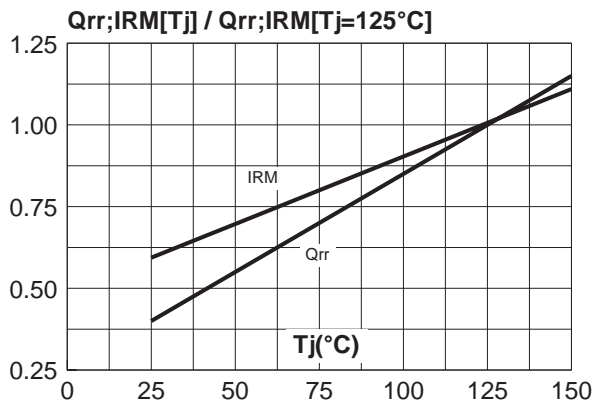
**Fig. 8:** Recovery charges versus  $dI_F/dt$



**Fig. 9:** Peak reverse recovery current versus  $dI_F/dt$ .

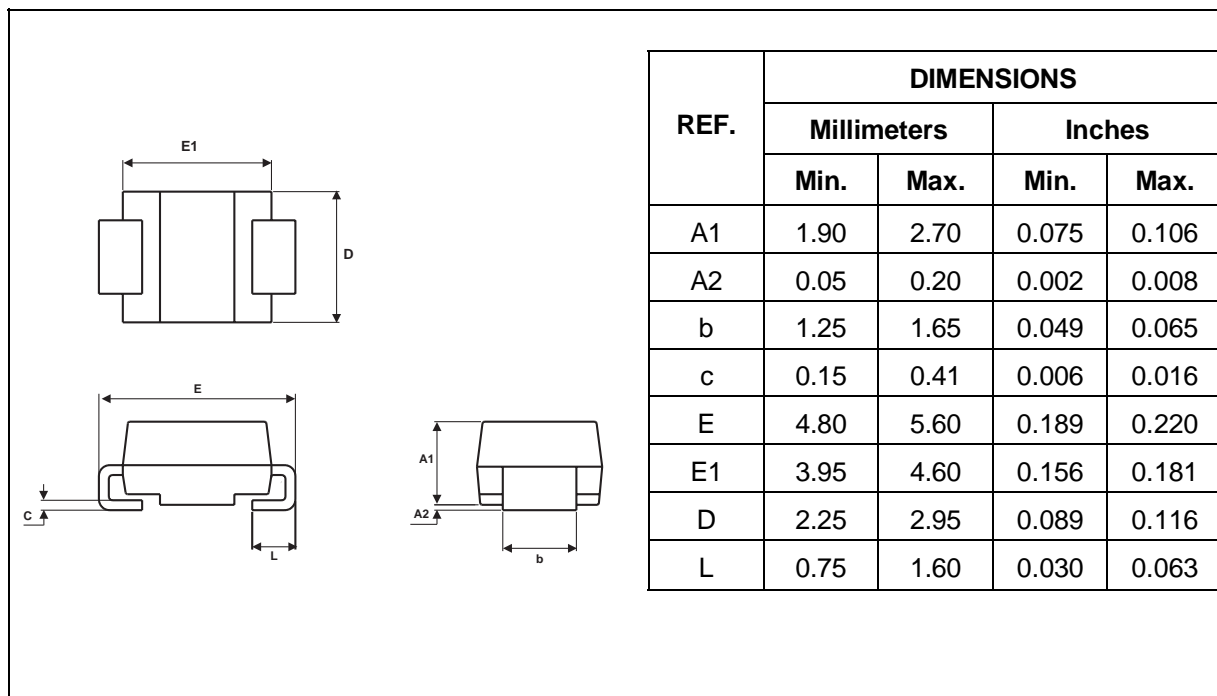


**Fig. 10:** Dynamic parameters versus junction temperature.

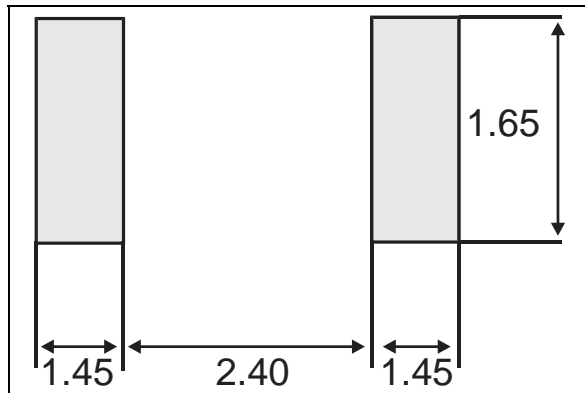


## PACKAGE MECHANICAL DATA

## SMA



## FOOT PRINT (in millimeters)



- **Marking** : R12
- Cathode band is inked

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